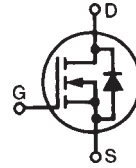


Polar™ HiPerFET™ Power MOSFET

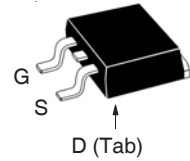
N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

IXFA6N120P
IXFP6N120P
IXFH6N120P

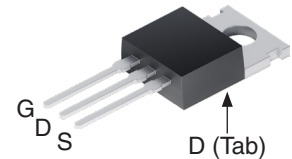


$$\begin{aligned} V_{DSS} &= 1200V \\ I_{D25} &= 6A \\ R_{DS(on)} &\leq 2.75\Omega \end{aligned}$$

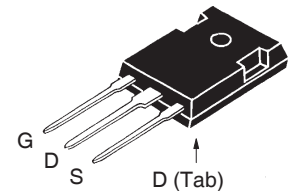
TO-263 AA (IXFA)



TO-220AB (IXFP)



TO-247 (IXFH)



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	1200	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1M\Omega$	1200	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	6	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	18	A
I_A	$T_C = 25^\circ\text{C}$	3	A
E_{AS}	$T_C = 25^\circ\text{C}$	300	mJ
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	250	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{sig}		-55 ... +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ\text{C}$
F_C	Mounting Force (TO-263)	10..65 / 2.2..14.6	N/lb
M_d	Mounting Torque (TO-247 & TO-220)	1.13 / 10	Nm/lb.in
Weight	TO-263	2.5	g
	TO-220	3.0	g
	TO-247	6.0	g

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu\text{A}$	1200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 1\text{mA}$	2.5		5.0 V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			10 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1			2.75 Ω

Features

- International Standard Packages
- Dynamic dv/dt Rating
- Avalanche Rated
- Fast Intrinsic Diode
- Low Q_G & $R_{DS(on)}$
- Low Drain-to-Tab Capacitance
- Low Package Inductance

Advantages

- Easy to Mount
- Space Savings

Applications

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- Uninterrupted Power Supplies
- AC Motor Drives
- High Speed Power Switching Applications

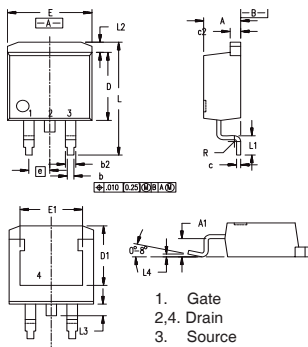
Symbol	Test Conditions	Characteristic Values		
	(T _J = 25°C, Unless Otherwise Specified)	Min.	Typ.	Max
g_{fs}	V _{DS} = 20V, I _D = 0.5 • I _{D25} , Note 1	3.0	5.0	S
R_{Gi}	Gate Input Resistance		1.8	Ω
C_{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz		2830	pF
C_{oss}			150	pF
C_{rss}			30	pF
t_{d(on)}	Resistive Switching Times V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25} R _G = 3Ω (External)		24	ns
t_r			11	ns
t_{d(off)}			60	ns
t_f			14	ns
Q_{g(on)}	V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25}		92	nC
Q_{gs}			15	nC
Q_{gd}			50	nC
R_{thJC}				0.50 °C/W
R_{thCS}	TO-220		0.50	°C/W
R_{thCS}	TO-247		0.21	°C/W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values		
	(T _J = 25°C, Unless Otherwise Specified)	Min.	Typ.	Max
I_S	V _{GS} = 0V			6 A
I_{SM}	Repetitive, Pulse Width Limited by T _{JM}			24 A
V_{SD}	I _F = I _S , V _{GS} = 0V, Note 1			1.4 V
t_{rr}	I _F = 3A, V _{GS} = 0V -di/dt = 100A/μs V _R = 100V			300 ns
I_{RM}			7.8	A
Q_{RM}			1.1	μC

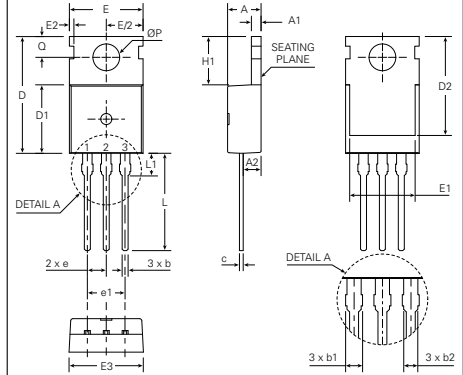
Note 1: Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

TO-263 Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.40	0.74	.016	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	8.00	8.89	.280	.320
E	9.65	10.41	.380	.405
E1	6.22	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.13	0	.005

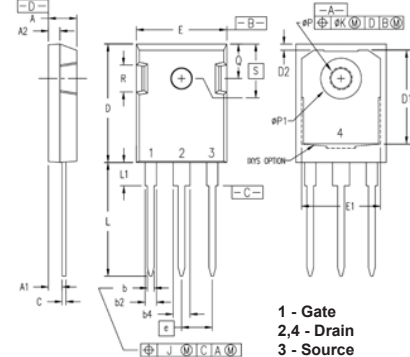
TO-220 Outline



Pins: 1 - Gate
3 - Source
2 - Drain

Symbol	Inches			Millimeters		
	Min.	Typical	Max.	Min.	Typical	Max
A	0.169	0.177	0.185	4.30	4.50	4.70
A1	0.049	0.051	0.055	1.25	1.30	1.40
A2	0.087	0.094	0.102	2.20	2.40	2.60
b	0.028	0.031	0.035	0.70	0.80	0.90
b1	0.056	0.060	0.064	1.42	1.52	1.62
b2	0.046	0.050	0.054	1.17	1.27	1.37
c	0.018	0.020	0.024	0.45	0.50	0.60
D	0.610	0.618	0.626	15.50	15.70	15.90
D1	0.354	0.362	0.370	9.00	9.20	9.40
D2	0.516	0.524	0.531	13.10	13.30	13.50
E	0.382	0.390	0.400	9.70	9.90	10.10
E1		0.346			8.80	
E2		0.024			0.60	
E3	0.386	0.394	0.402	9.80	10.00	10.20
e		0.100			2.54 BSC	
e1		0.200			5.08 BSC	
H1	0.248	0.256	0.264	6.30	6.50	6.70
L	0.507	0.515	0.523	12.88	13.08	13.28
L1		0.118			3.00	
OP	0.134	0.142	0.150	3.40	3.60	3.80
Q	0.106	0.110	0.114	2.70	2.80	2.90

TO-247 Outline



1 - Gate
2,4 - Drain
3 - Source

Dim.	Millimeter		Inches	
	min	max	min	max
A	4.70	5.30	0.185	0.209
A1	2.21	2.59	0.087	0.102
A2	1.50	2.49	0.059	0.098
b	0.99	1.40	0.039	0.055
b2	1.65	2.39	0.065	0.094
b4	2.59	3.43	0.102	0.135
c	0.38	0.89	0.015	0.035
D	20.79	21.45	0.819	0.845
D1	13.07	-	0.515	-
D2	0.51	1.35	0.020	0.053
E	15.48	16.24	0.610	0.640
E1	13.45	-	0.53	-
E2	4.31	5.48	0.170	0.216
e	5.45 BSC		0.215 BSC	
L	19.80	20.30	0.078	0.800
L1	-	4.49	-	0.177
OP	3.55	3.65	0.140	0.144
OP1	-	7.39	-	0.290
Q	5.38	6.19	0.212	0.244
S	6.14 BSC		0.242 BSC	

Littelfuse Reserves the Right to Change Limits, Test Conditions, and Dimensions.

LF MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065B1	6,683,344	6,727,585	7,005,734B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123B1	6,534,343	6,710,405B2	6,759,692	7,063,975B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728B1	6,583,505	6,710,463	6,771,478B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

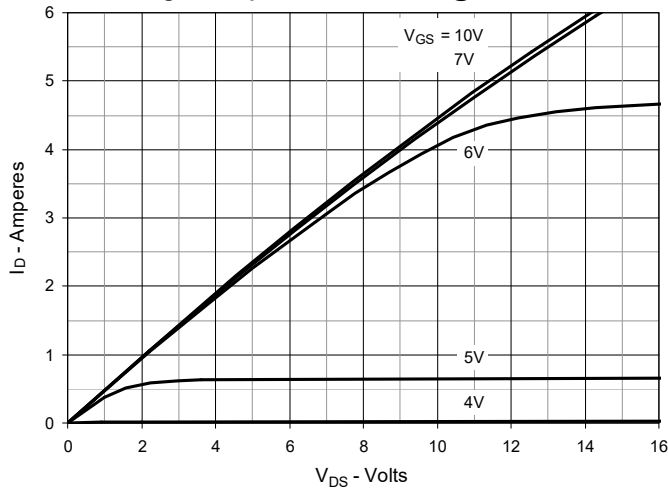


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

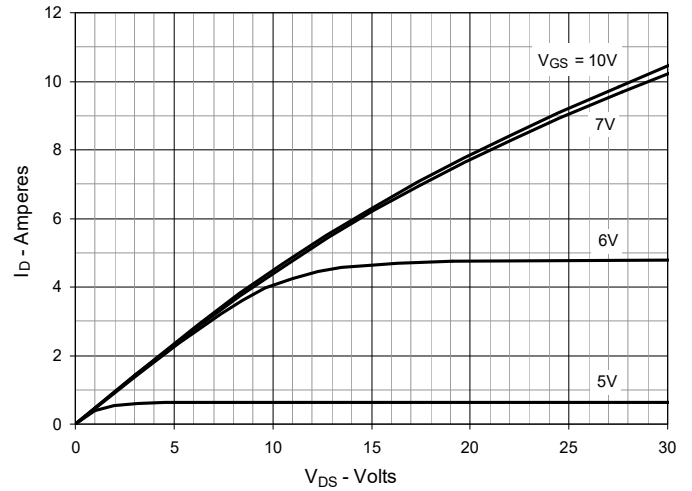


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

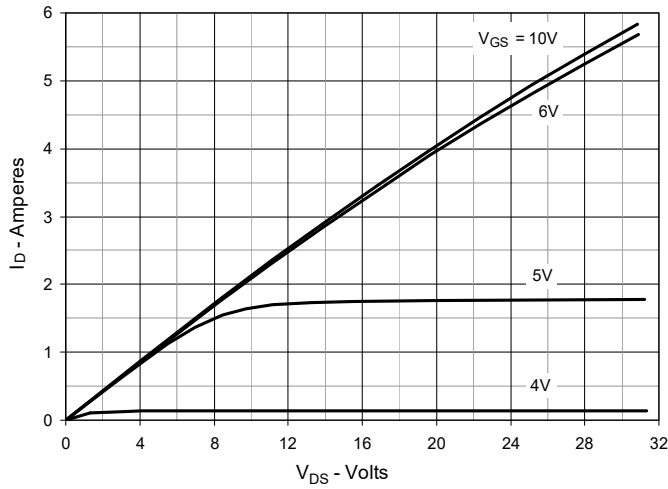


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 3\text{A}$ Value vs. Junction Temperature

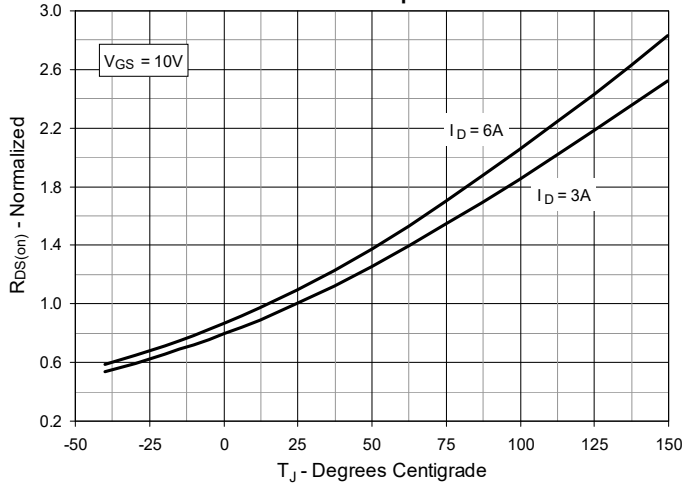


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 3\text{A}$ Value vs. Drain Current

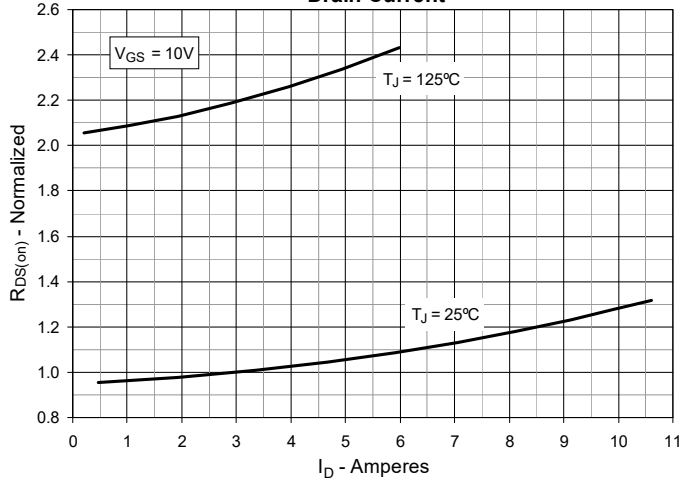


Fig. 6. Maximum Drain Current vs. Case Temperature

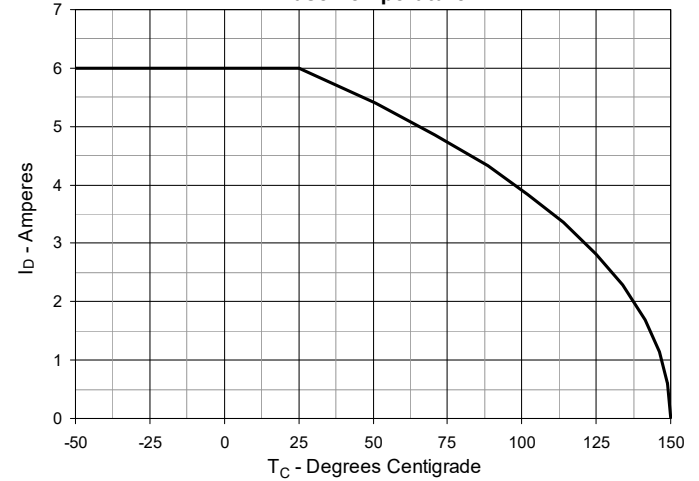


Fig. 7. Input Admittance

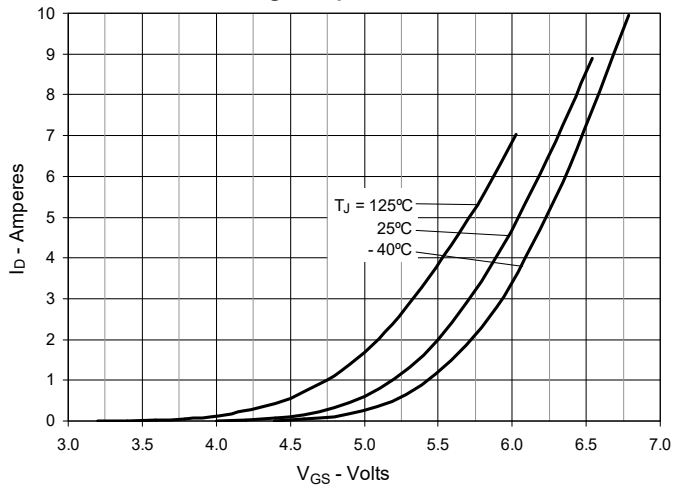


Fig. 8. Transconductance

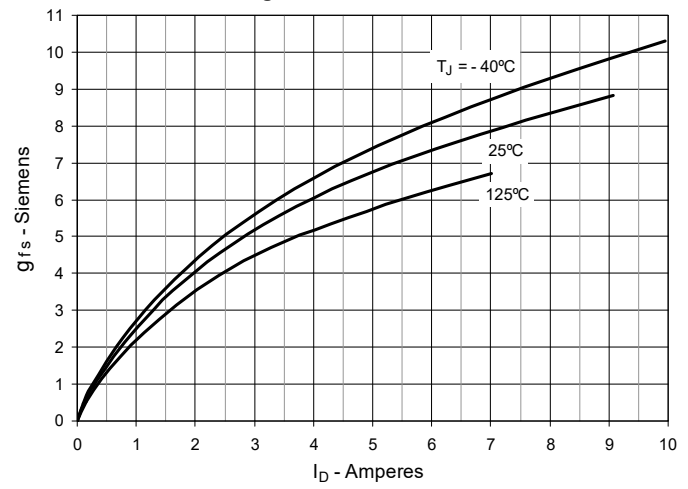


Fig. 9. Forward Voltage Drop of Intrinsic Diode

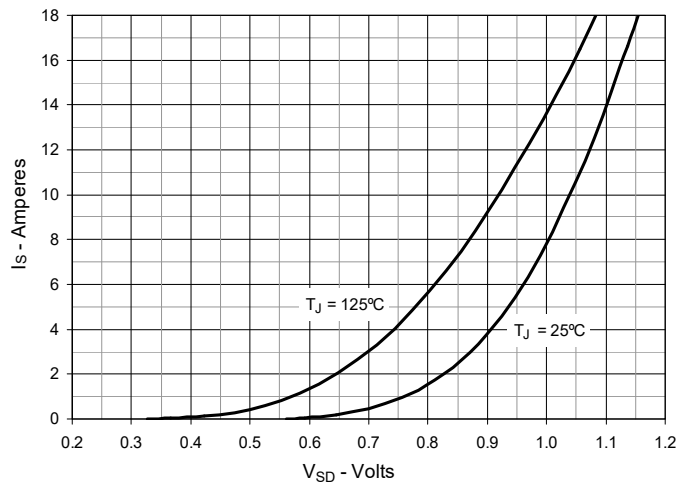


Fig. 10. Gate Charge

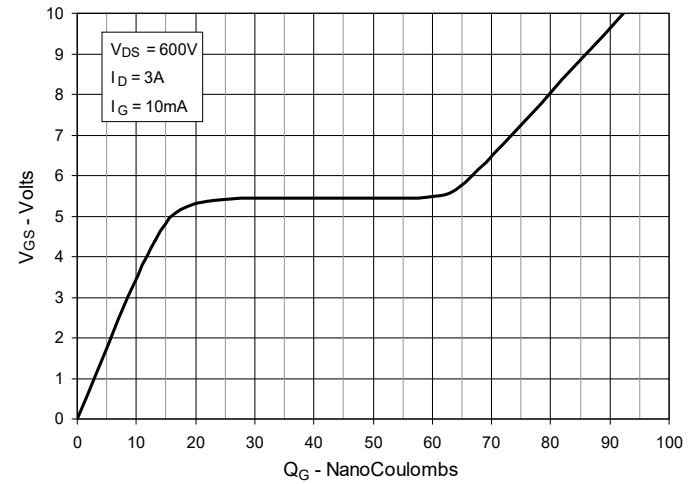


Fig. 11. Capacitance

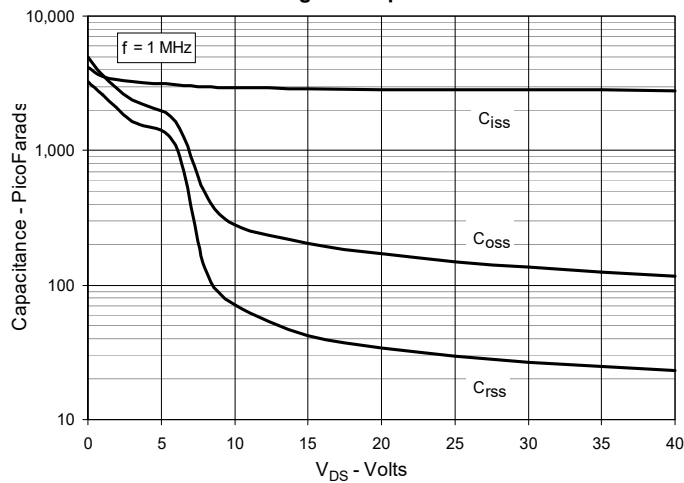


Fig.12. Forward-Bias Safe Operating Area

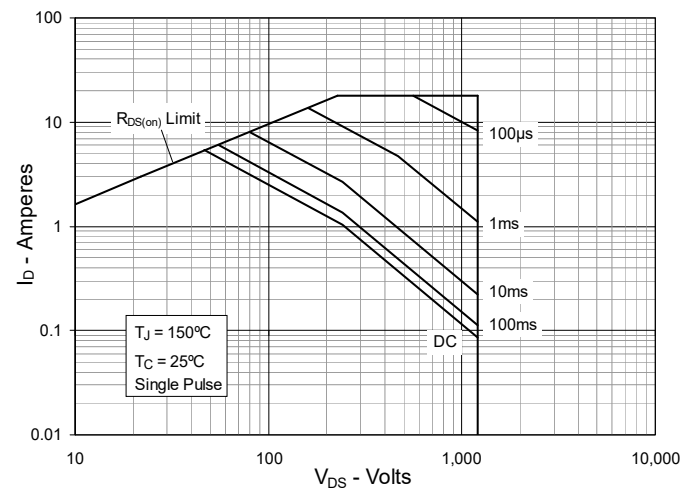
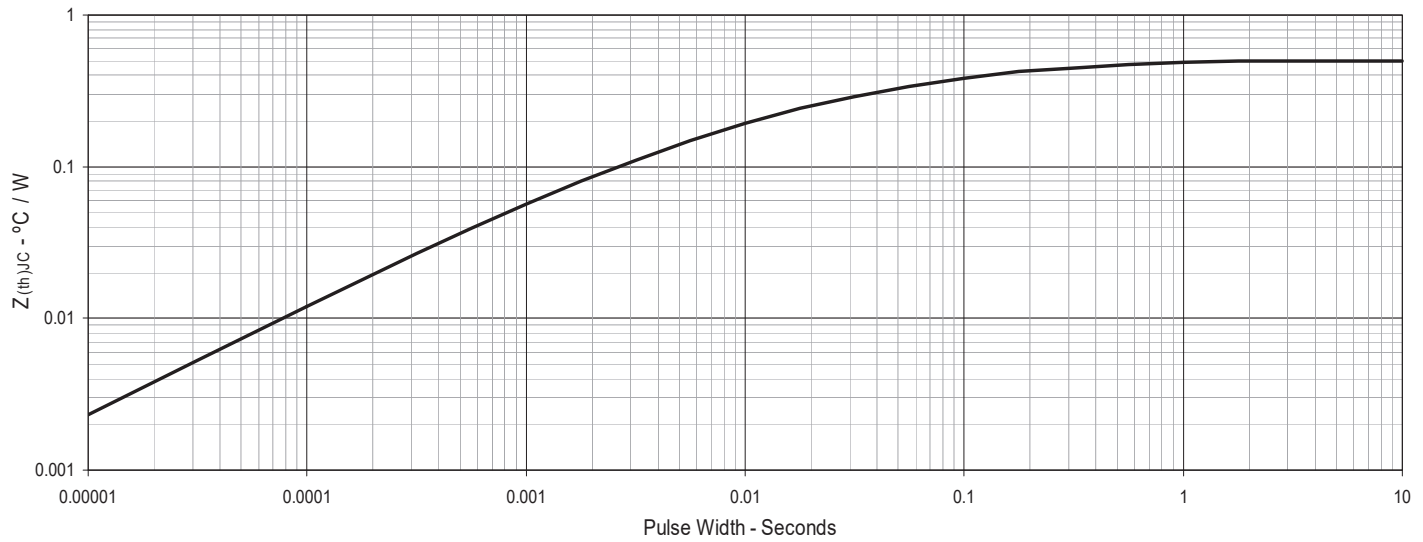


Fig. 13. Maximum Transient Thermal Impedance

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Part of:

